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# SSCN2222AGS8

#### **High Frequency High Gain NPN Power BJT**

#### > Features

VCB	VCE	VEB	IC	
75V	40V	6V	600mA	

#### > Description

This product is general usage and suitable for many different applications. It can be used for medium power amplifiers and switches requiring collector currents up to 600 mA.

# 1 - Base 2 - Emitter

SOT-523

Pin configuration

 $\triangleright$ 

### > Applications

- Low current and high precision circuits such preamplifiers, oscillators, current mirror configuration
- Medium power amplification and switching

#### > Ordering Information

Device	Package	Shipping	
SSCN2222AGS8	SOT-523	3000/Reel	







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# > Absolute Maximum Ratings( $T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	75	V
Collector- Emitter Voltage	Vceo	40	V
Emitter-Base Voltage	Vebo	6	V
Collector Current-Continuous	lc	600	mA
Collector Power Dissipation	Pc	150	mW
Junction Temperature	TJ	150	°C
Storage Temperature	T <sub>STG</sub>	-55 to 150	°C

# > Electrical Characteristics ( $T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	I <sub>C</sub> = 10uA,I <sub>E</sub> =0 75				V
Collector-emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =10mA,I <sub>B</sub> =0 40				V
Emitter -Base Breakdown Voltage	BV <sub>EBO</sub>	I <sub>E</sub> =10uA,I <sub>C</sub> =0	c=0 6			V
Collector Cutoff Current	ICEX	V <sub>CE</sub> =60V, V <sub>BE</sub> =3V			10	nA
	h <sub>FE1</sub>	V <sub>CE</sub> =10V,I <sub>C</sub> =150mA	100		300	
	h <sub>FE2</sub>	V <sub>CE</sub> =10V,I <sub>C</sub> =0.1mA	35			
DC Current Gain	h <sub>FE3</sub>	V <sub>CE</sub> =10V,I <sub>C</sub> = 1mA	50			
	h <sub>FE4</sub>	V <sub>CE</sub> =10V,I <sub>C</sub> = 10mA	75			
	h <sub>FE5</sub>	V <sub>CE</sub> =10V,I <sub>C</sub> = 500mA	40			
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =500mA,I <sub>B</sub> =50mA			1.0	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	Ic=500mA,I <sub>B</sub> =50mA			2.0	V
Transition frequency	f⊤	V <sub>CE</sub> =20V,Ic=20mA f=100MHz	300			MHz
Delay Time	t <sub>d</sub>	V <sub>CC</sub> =30V,I <sub>C</sub> =150mA, I <sub>B1</sub> =15mA			10	ns
Rise Time	tr	V <sub>cc</sub> =30V,I <sub>c</sub> =150mA, I <sub>B1</sub> =15mA			25	ns
Storage Time	ts	V <sub>CC</sub> =30V,I <sub>C</sub> =150mA,			225	ns
<b>3</b> • • • • • •		I <sub>B1</sub> = I <sub>B2</sub> =15mA				
   Fall Time	t <sub>f</sub>	V <sub>CC</sub> =30V,I <sub>C</sub> =150mA,	/ <sub>cc</sub> =30V,I <sub>c</sub> =150mA,		60	ns
	4	I <sub>B1</sub> = I <sub>B2</sub> =15mA			00	



1

0.8

0.6

0.4

0.2

0

1

**Base-Emitter Saturation** 

Voltage\_V<sub>BEsat</sub>(V)

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## > Typical Performance Characteristics ( $T_A=25^{\circ}C$ unless otherwise noted)



**Collector Current vs. Base-Emitter Voltage** 

T\_=25°C

T<sub>A</sub>=100°C

100

**β=10** 



DC Current Gain vs. Collector Current



V<sub>BE(sat)</sub> vs. Collector Current

Collector Current\_Ic(mA)

10





V<sub>CE(sat)</sub> vs. Collector Current



#### **Transition Frequency vs. Collector Current**



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## > Package Information







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	0.700	0.900	0.028	0.035	
A1	0.000	0.100	0.000	0.004	
A2	0.700	0.800	0.028	0.031	
b1	0.150	0.250	0.006	0.010	
b2	0.250	0.350	0.010	0.014	
С	0.100	0.200	0.004	0.008	
D	1.500	1.700	0.059	0.067	
E	0.700	0.900	0.028	0.035	
E1	1.450	1.750	0.057	0.069	
е	0.500 TYP.		0.020 TYP.		
e1	0.900	1.100	0.035	0.043	
L	0.400 REF.		0.016 REF.		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

# > SOT-523 Suggested Pad Layout



#### Note:

1.Controlling dimension:in millimeters.

2.General tolerance:±0.05mm.

3. The pad layout is for reference purposes only.



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